

In re: Satoshi Watanabe

Serial No.: 10/052,687

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Page 2 of 6

In the Claims:

1. (Original) A resist material comprising:
 - (A) an organic solvent,
 - (B) a resin which exhibits transmittance of 30%/.mu.m or greater at a wavelength of 193 nm, is an alkali insoluble or alkali sparingly soluble resin protected with an acid labile group, and has an alicyclic structure having a - (CO)-O-(CO)_k - group (in which, k stands for 0 or 1) which becomes alkali soluble upon dissociation of said acid labile group,
 - (C) a photoacid generator,
 - (D) a basic compound, and
 - (E) at least one compound selected from the group consisting of thiol derivatives, disulfide derivatives and thiol sulfonate derivatives.
2. (Original) A resist material of claim 1, wherein the thiol derivatives are each free of a carbon-carbon double bond.
3. (Original) A resist material of claim 1, further comprising (F) a dissolution inhibitor.
4. (Original) A resist material of claim 2, further comprising (F) a dissolution inhibitor.
5. (Original) A resist material according to claim 1, further comprising (G) a surfactant.
6. (Original) A resist material according to claim 2, further comprising (G) a surfactant.
7. (Original) A resist material according to claim 3, further comprising (G) a surfactant.
8. (Original) A resist material according to claim 4, further comprising (G) a surfactant.

9. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 1 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

10. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 2 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

11. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 3 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

12. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 4 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

13. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 5 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

14. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 6 onto a substrate; after a heat treatment, exposing the resist material

to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

15. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 7 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.

16. (Original) A pattern forming method, which comprises steps of applying a resist material according to claim 8 onto a substrate; after a heat treatment, exposing the resist material to a high energy beam or electron beam through a photomask; and after an optional heat treatment, developing the resist material with a developer.